

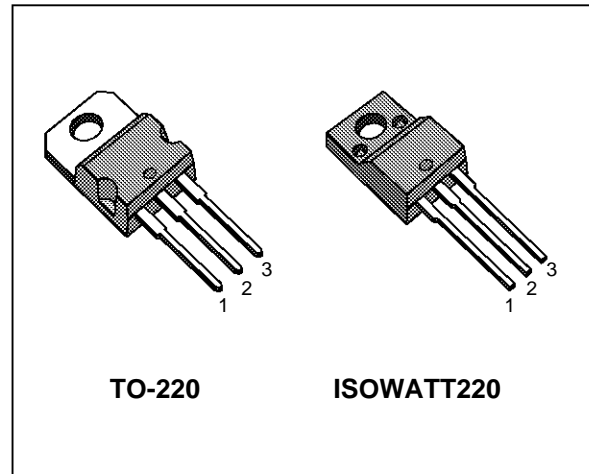
## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
IRF520	100 V	< 0.27 Ω	10 A
IRF520FI	100 V	< 0.27 Ω	7 A

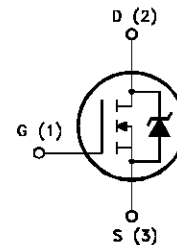
- TYPICAL R<sub>DS(on)</sub> = 0.23 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		IRF520	IRF520FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	100		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	100		V
V <sub>GS</sub>	Gate-source Voltage	± 20		V
I <sub>D</sub>	Drain Current (cont.) at T <sub>c</sub> = 25 °C	10	7	A
I <sub>D</sub>	Drain Current (cont.) at T <sub>c</sub> = 100 °C	7	5	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	40	40	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	70	35	W
	Derating Factor	0.47	0.23	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	2000	V
T <sub>stg</sub>	Storage Temperature	-65 to 175		°C
T <sub>j</sub>	Max. Operating Junction Temperature	175		°C

(●) Pulse width limited by safe operating area

**THERMAL DATA**

		TO-220	ISOWATT220		
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	2.14	4.29	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5		°C/W
R <sub>thc-s</sub>	Thermal Resistance Case-sink	Typ	0.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

**AVALANCHE CHARACTERISTICS**

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	10	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	36	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)	9	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%)	7	A

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C			250 1000	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	2.9	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 5 A		0.23	0.27	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	10			A

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> I <sub>D</sub> = 5 A	2.7	4.5		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		330	450	pF
C <sub>oss</sub>	Output Capacitance			90	120	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25	40	pF

**ELECTRICAL CHARACTERISTICS** (continued)  
**SWITCHING RESISTIVE LOAD**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 50\text{ V}$ $I_D = 5\text{ A}$		10	15	ns
$t_r$	Rise Time	$R_{GS} = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		50	75	ns
$t_{d(off)}$	Turn-off Delay Time	(see test circuit)		25	40	ns
$t_f$	Fall Time			20	30	ns
$Q_g$	Total Gate Charge	$I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$		15	25	nC
$Q_{gs}$	Gate-Source Charge	$V_{DD} = \text{Max Rating} \times 0.8$		7		nC
$Q_{gd}$	Gate-Drain Charge	(see test circuit)		4		nC

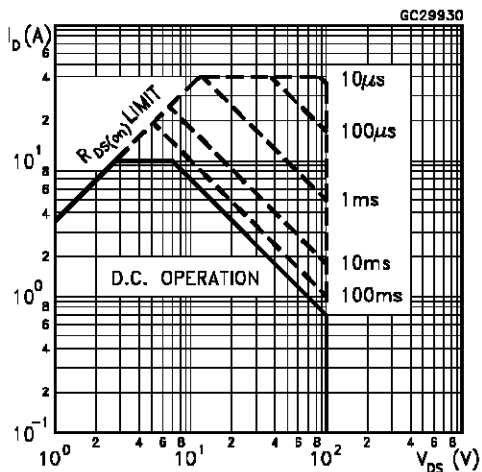
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				10	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				40	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 10\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 10\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		80		ns
$Q_{rr}$	Reverse Recovery Charge			0.22		$\mu\text{C}$

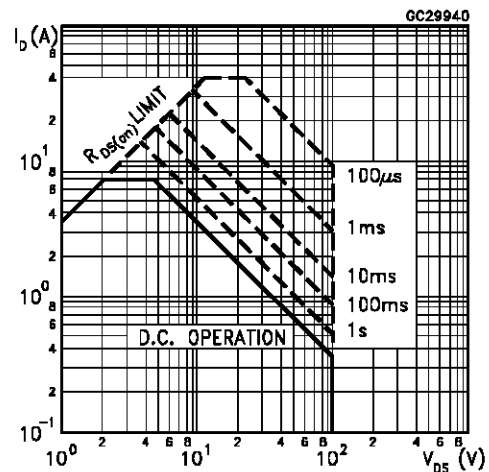
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

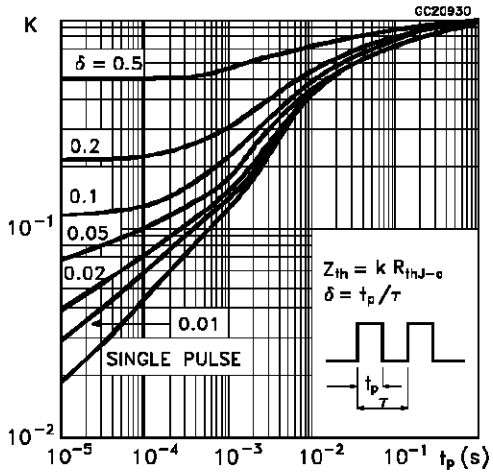
Safe Operating Area for TO-220



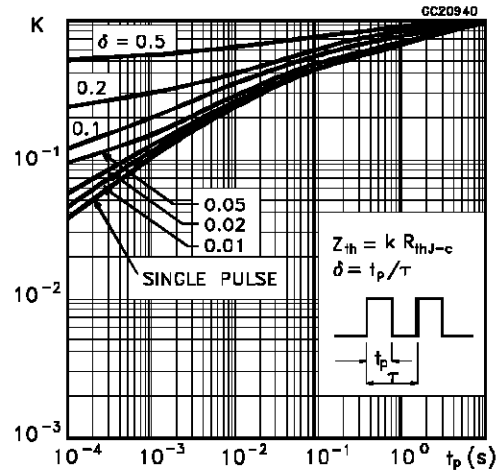
Safe Operating Area for ISOWATT220



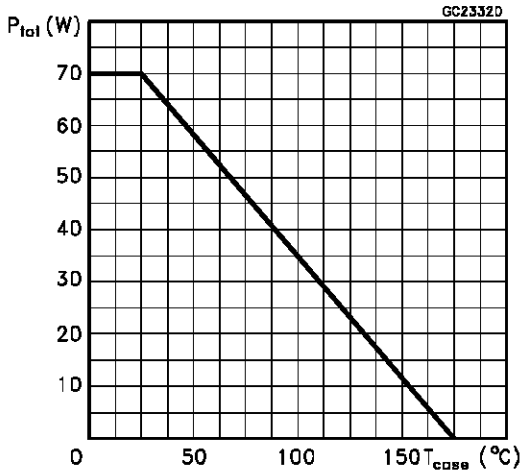
Thermal Impedance for TO-220



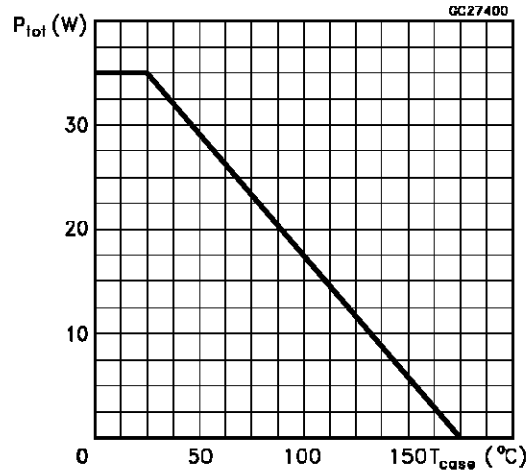
Thermal Impedance for ISOWATT220



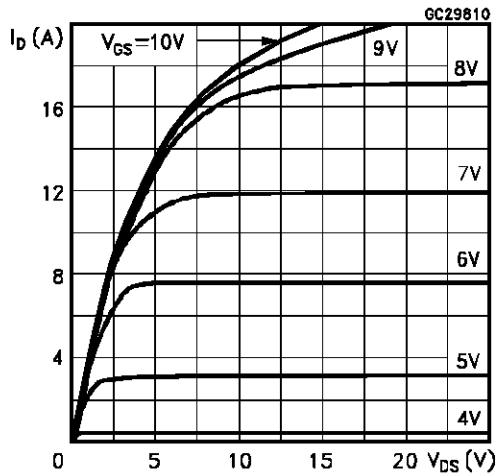
Derating Curve for TO-220



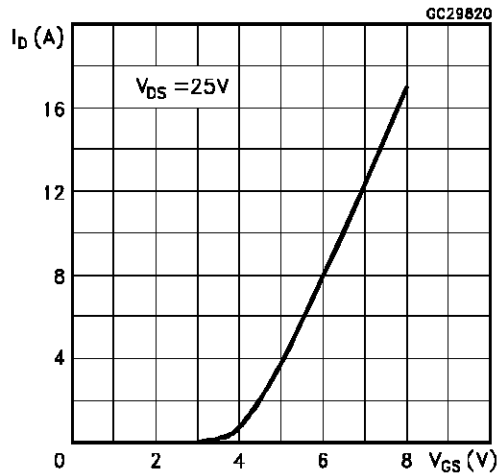
Derating Curve for ISOWATT220



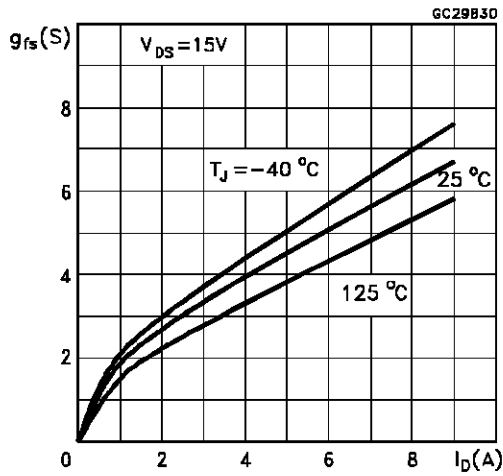
Output Characteristics



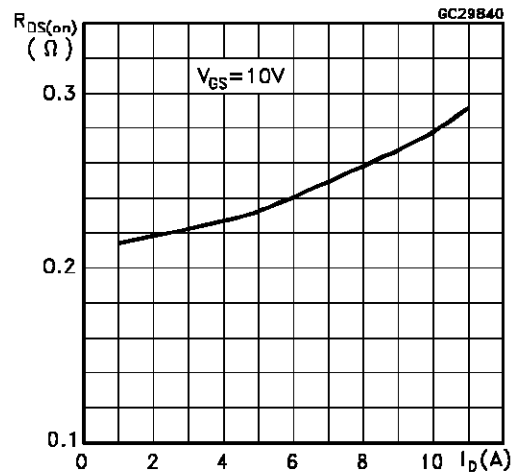
Transfer Characteristics



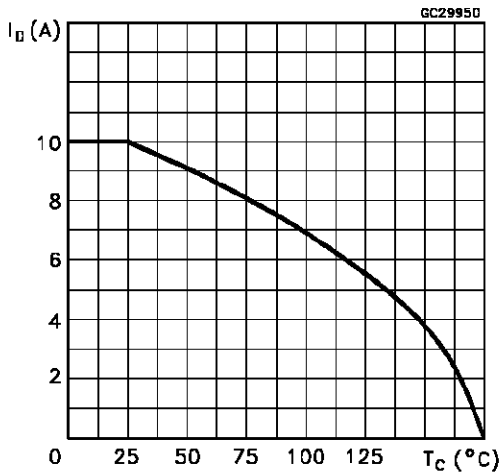
Transconductance



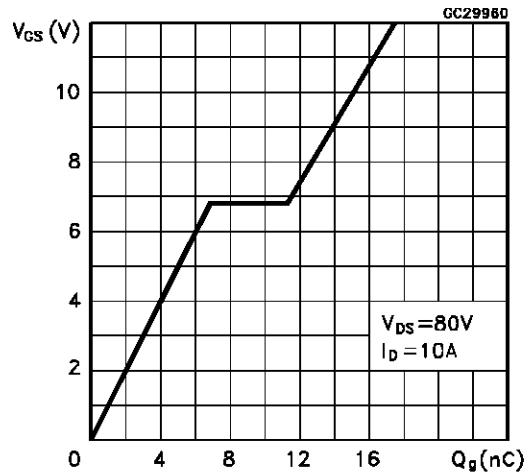
Static Drain-source On Resistance



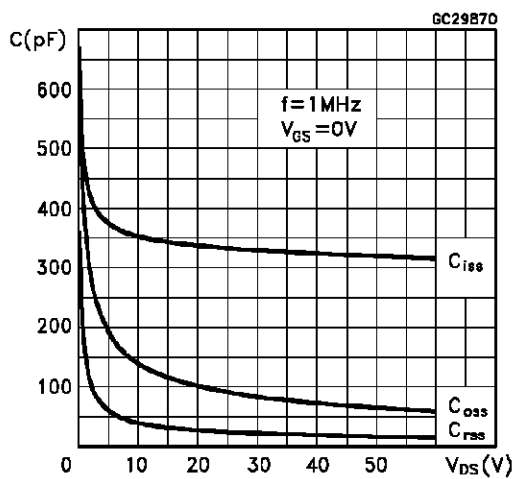
Maximum Drain Current vs Temperature



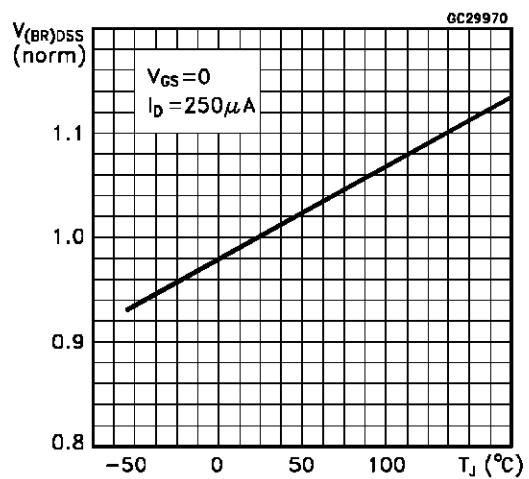
Gate Charge vs Gate-source Voltage



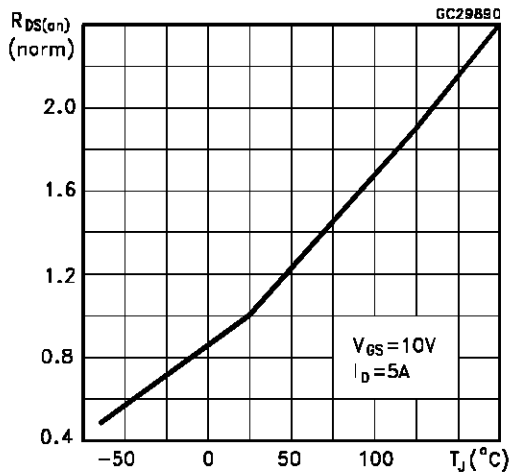
Capacitance Variations



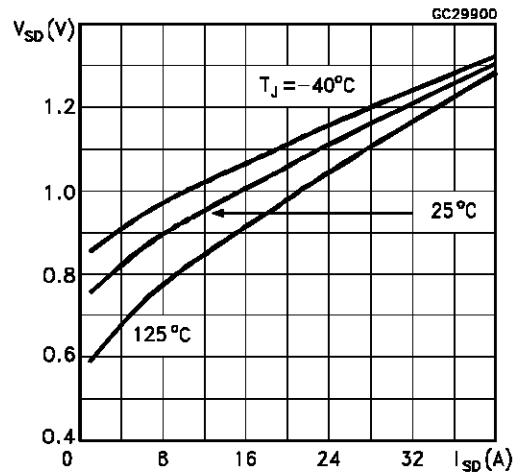
Normalized Breakdown Voltage vs Temperature



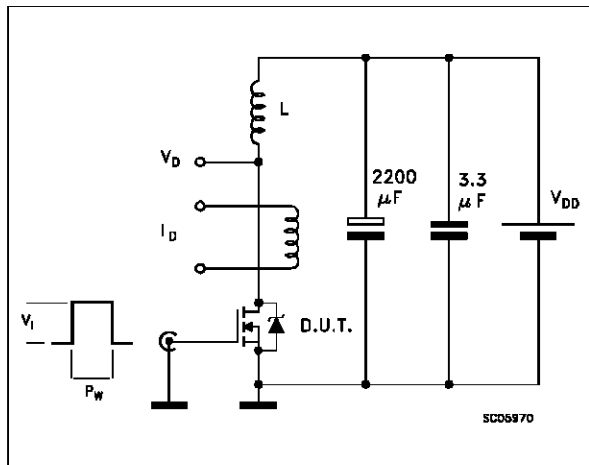
Normalized On Resistance vs Temperature



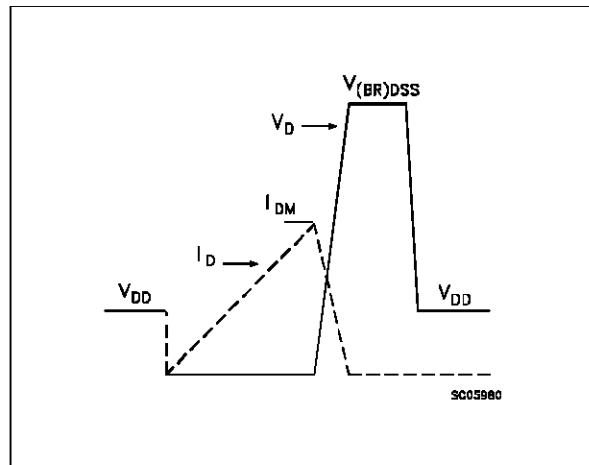
Source-drain Diode Forward Characteristics



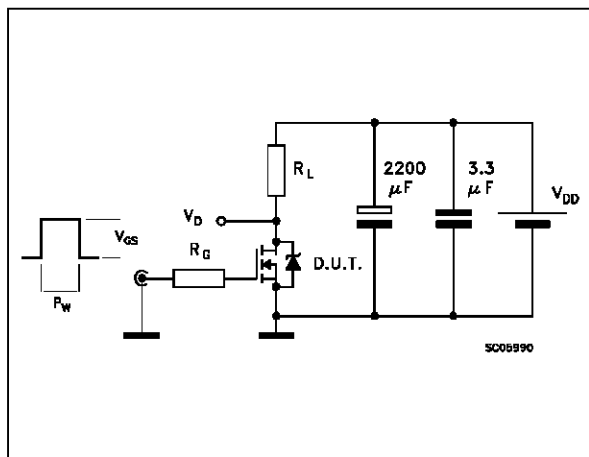
Unclamped Inductive Load Test Circuit



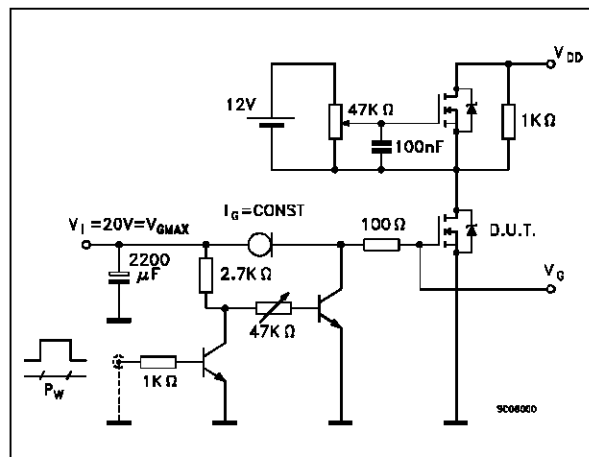
Unclamped Inductive Waveforms



Switching Time Test Circuit

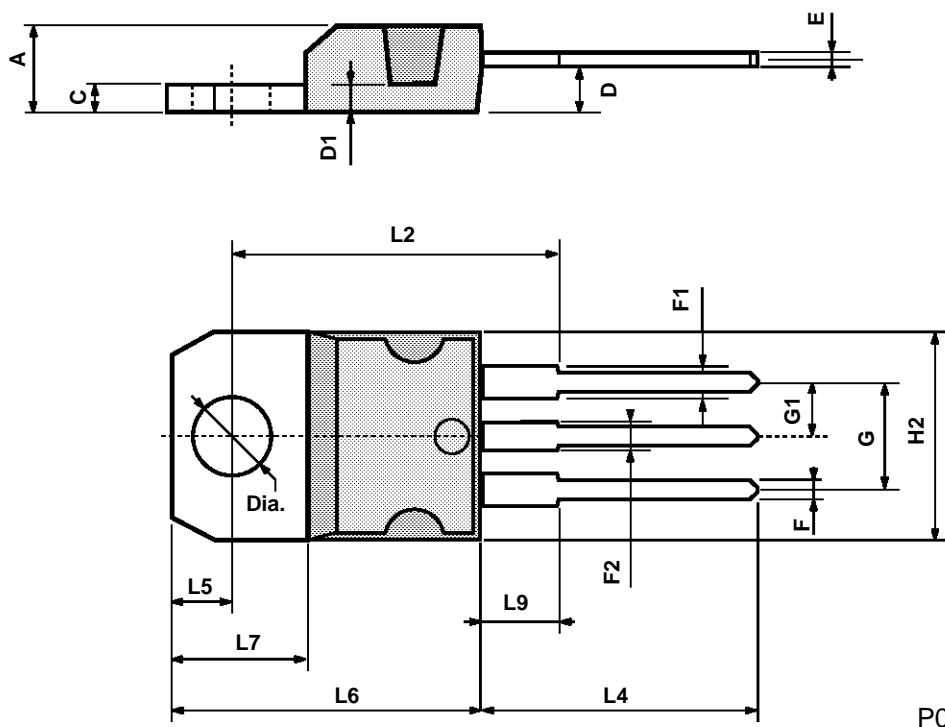


Gate Charge Test Circuit



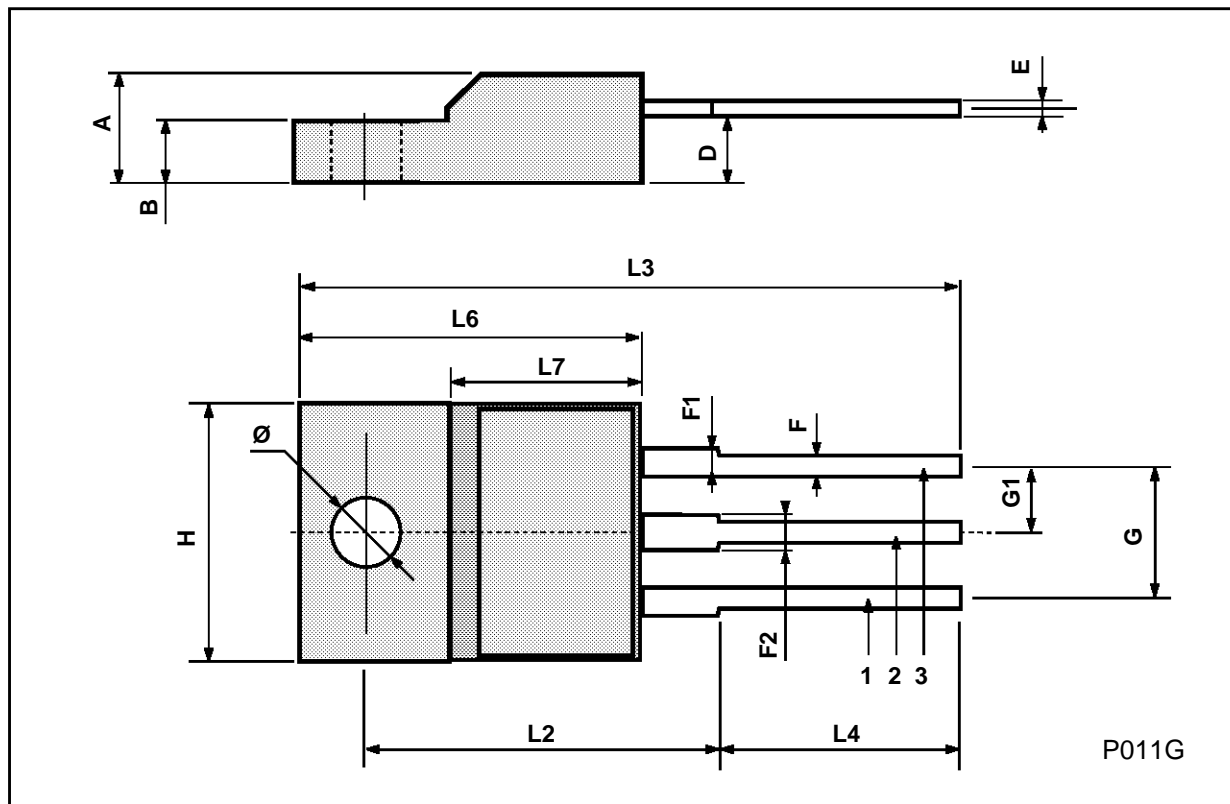
## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



**ISOWATT220 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126





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